

General Description

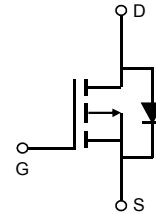
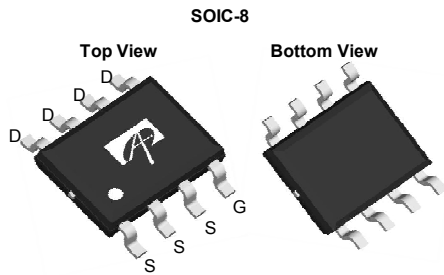
• The AO4413 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

• RoHS and Halogen-Free Compliant

Product Summary

V_{DS}	-30V
I_D (at $V_{GS}=-20V$)	-15A
$R_{DS(ON)}$ (at $V_{GS}=-20V$)	< 7m Ω
$R_{DS(ON)}$ (at $V_{GS} = -10V$)	< 8.5m Ω

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	-15
		$T_A=70^\circ\text{C}$	-12.8
Pulsed Drain Current ^C	I_{DM}	-120	A
Avalanche Current ^C	I_{AS}, I_{AR}	50	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	125	mJ
Power Dissipation ^B	P_D	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	59	75
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±25V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-2.5	-3.5	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-120			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-20V, I _D =-15A T _J =125°C		5.3 7.5	7 9	mΩ
		V _{GS} =-10V, I _D =-15A		6.4	8.5	
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-15A		35		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz	2310	2890	3500	pF
C _{oss}	Output Capacitance		410	585	760	pF
C _{rss}	Reverse Transfer Capacitance		280	470	660	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.9	3.8	5.7	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-15A	40	51	61	nC
Q _{gs}	Gate Source Charge		10	12	14	nC
Q _{gd}	Gate Drain Charge		10	16	22	nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =1.0Ω, R _{GEN} =3Ω		16		ns
t _r	Turn-On Rise Time			12		ns
t _{D(off)}	Turn-Off DelayTime			45		ns
t _f	Turn-Off Fall Time			22		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-15A, dI/dt=100A/μs	14	18	22	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-15A, dI/dt=100A/μs	9	11	13	nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

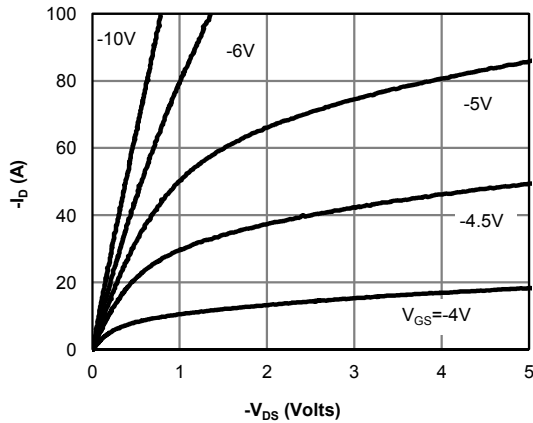


Figure 1: On-Region Characteristics (Note E)

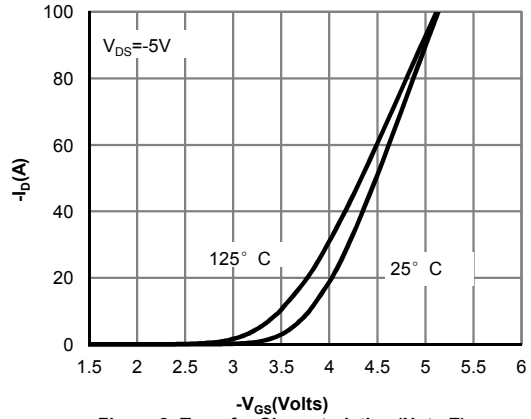


Figure 2: Transfer Characteristics (Note E)

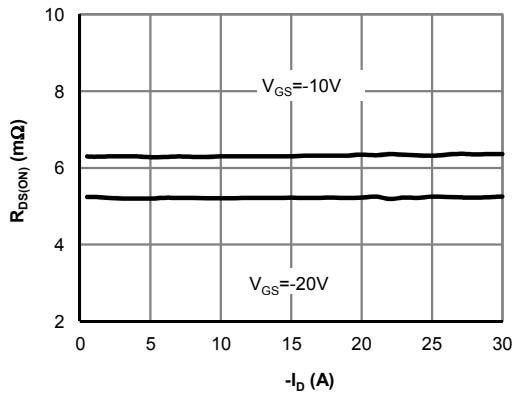


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

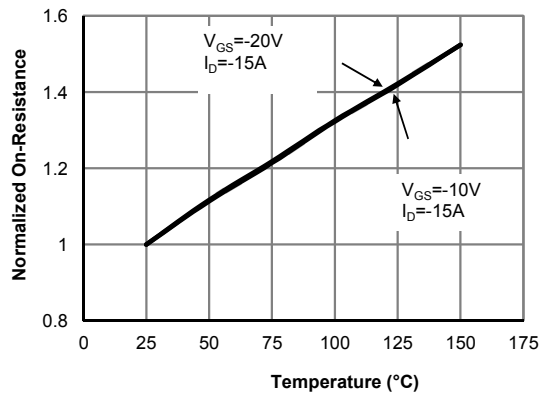


Figure 4: On-Resistance vs. Junction Temperature (Note E)

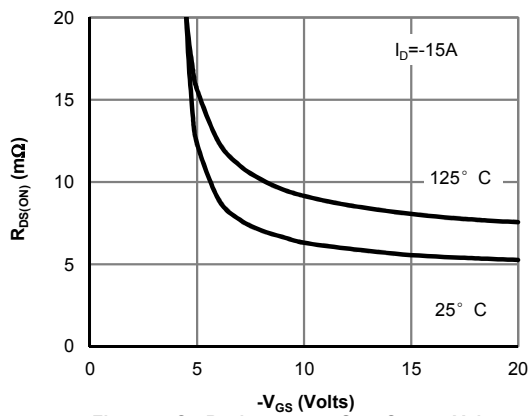


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

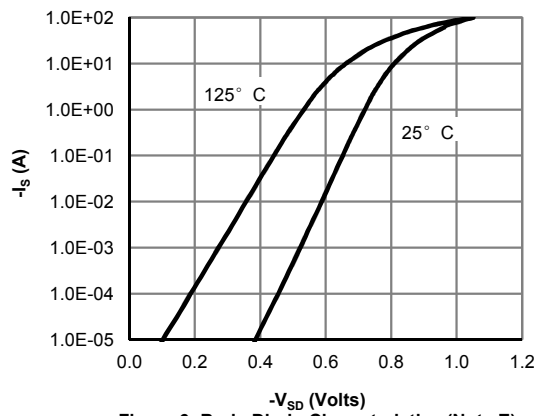


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

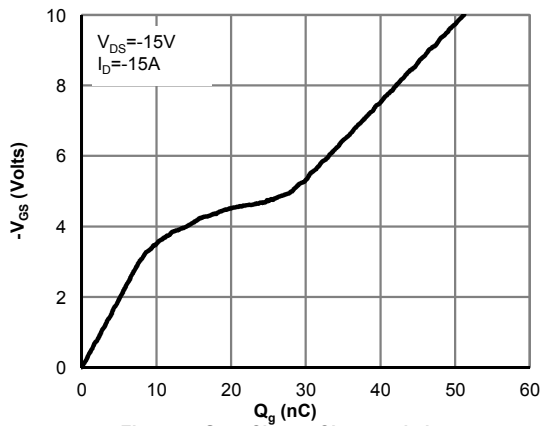


Figure 7: Gate-Charge Characteristics

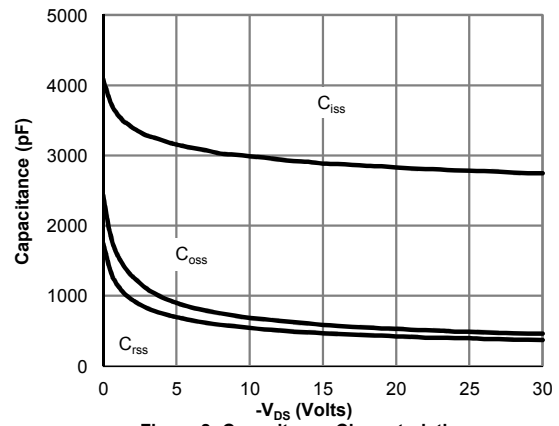


Figure 8: Capacitance Characteristics

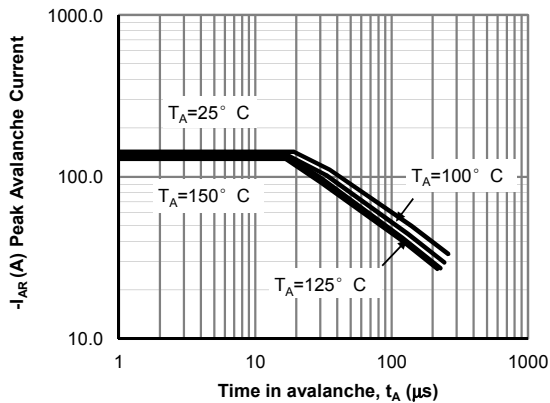


Figure 9: Single Pulse Avalanche capability (Note C)

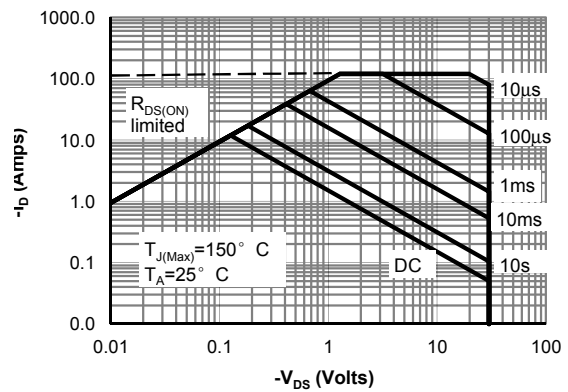


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

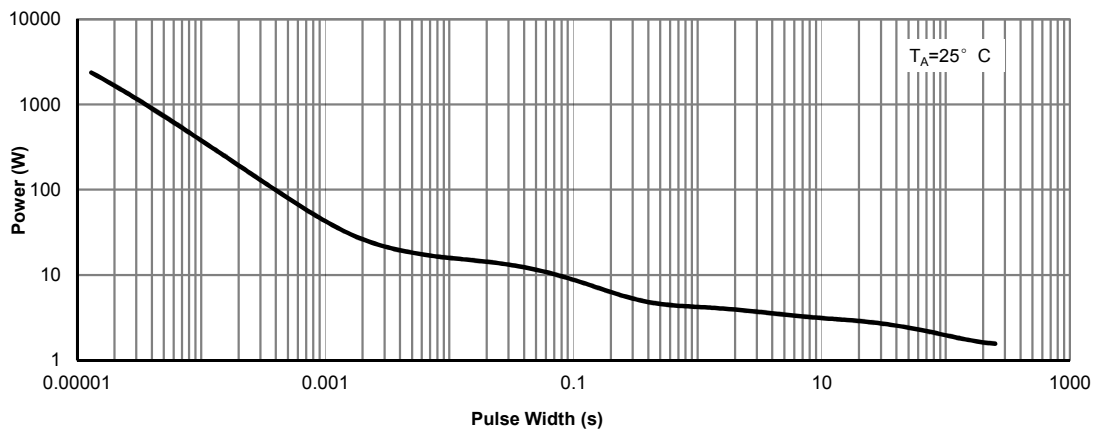


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

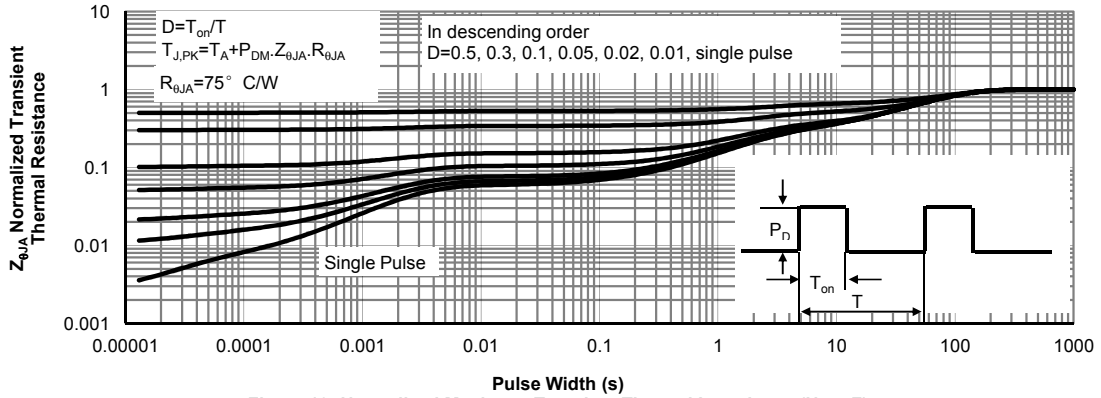
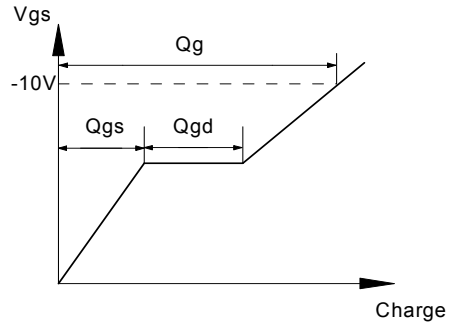
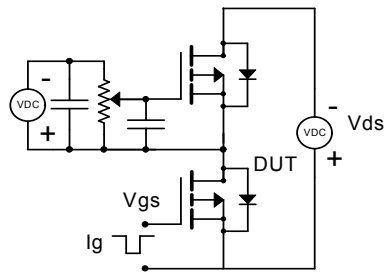
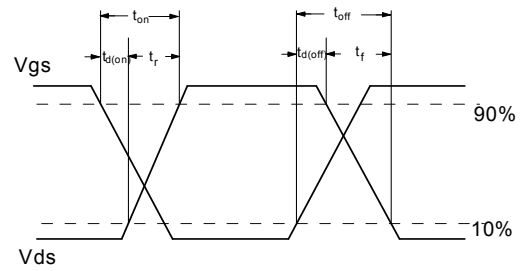
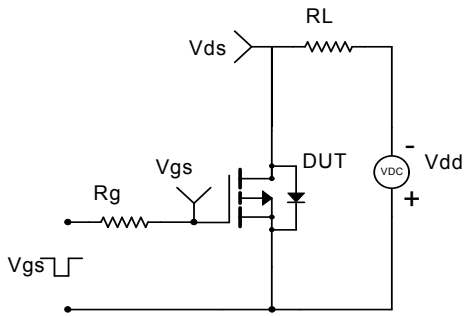


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

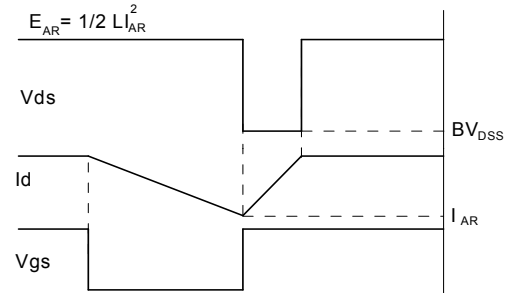
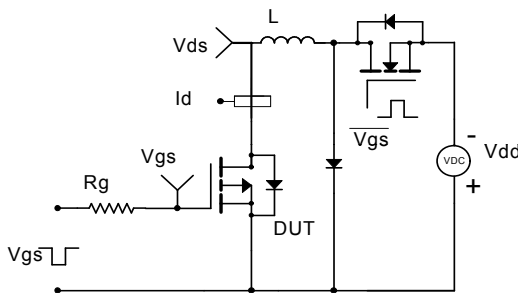
Gate Charge Test Circuit & Waveform



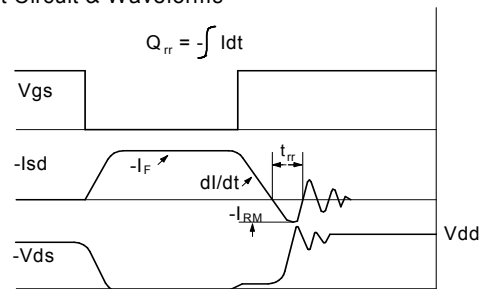
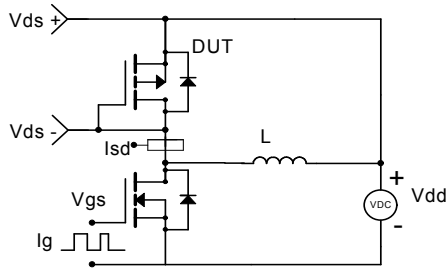
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms





Document No.	PD-00018
Version	F
Title	AO4413 Marking Description

SO-8 PACKAGE MARKING DESCRIPTION



Green product

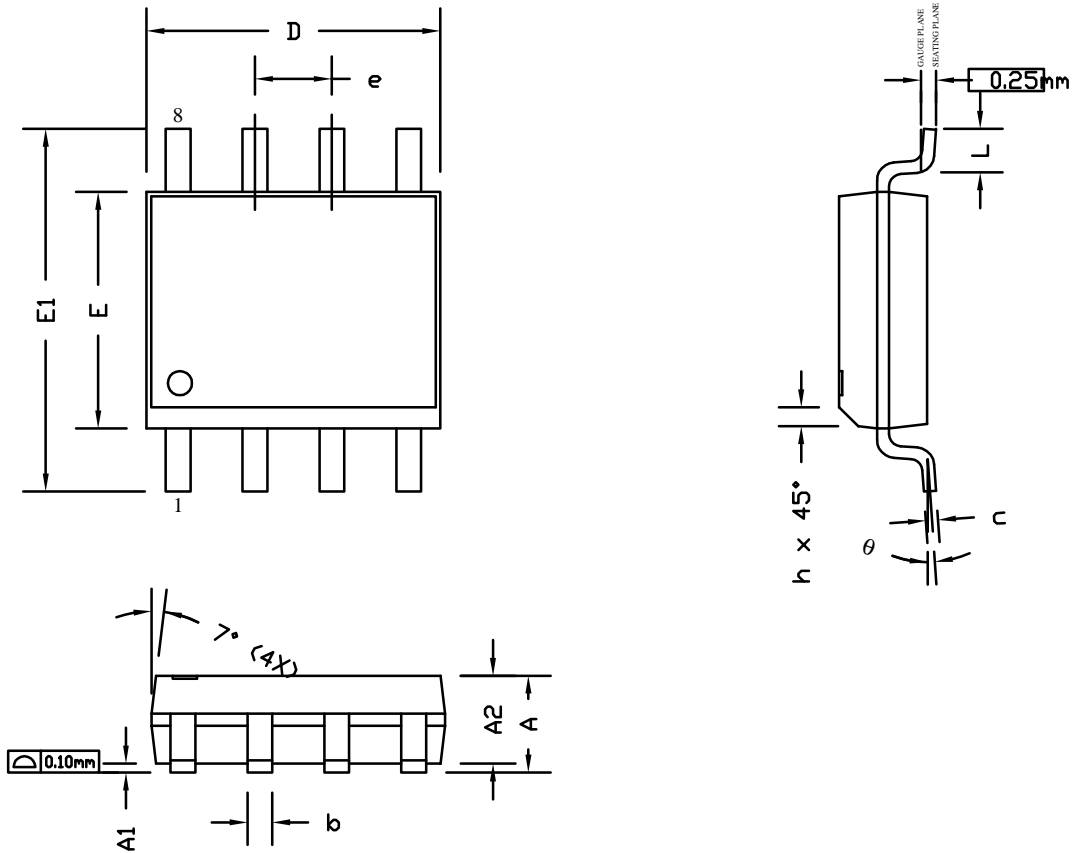
NOTE:

- LOGO - AOS Logo
- 4413 - Part number code
- F - Fab code
- A - Assembly location code
- Y - Year code
- W - Week code
- L&T - Assembly lot code

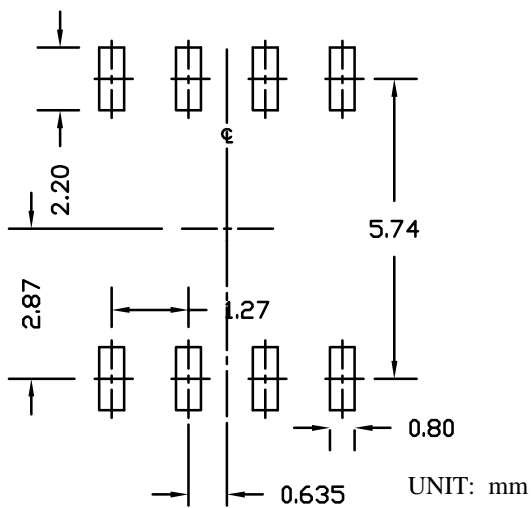
PART NO.	DESCRIPTION	CODE
AO4413	Green product	4413
AO4413L	Green product	4413



S08 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



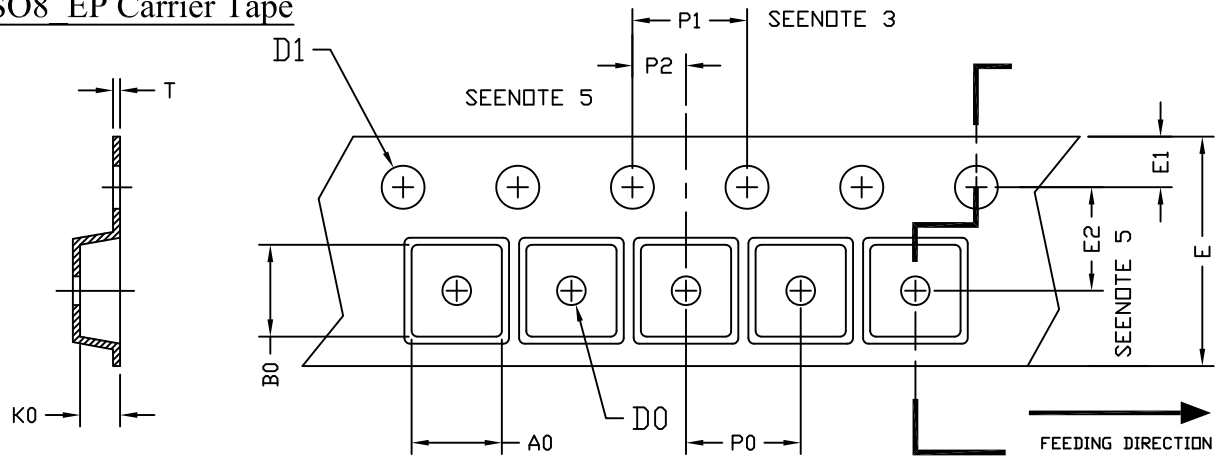
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35	1.65	1.75	0.053	0.065	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	1.25	1.50	1.65	0.049	0.059	0.065
b	0.31	0.41	0.51	0.012	0.016	0.020
c	0.17	0.20	0.25	0.007	0.008	0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	3.80	3.90	4.00	0.150	0.154	0.157
e	1.27 BSC			0.050 BSC		
E1	5.80	6.00	6.20	0.228	0.236	0.244
h	0.25	0.30	0.50	0.010	0.012	0.020
L	0.40	0.69	1.27	0.016	0.027	0.050
theta	0°	4°	8°	0°	4°	8°

NOTE

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



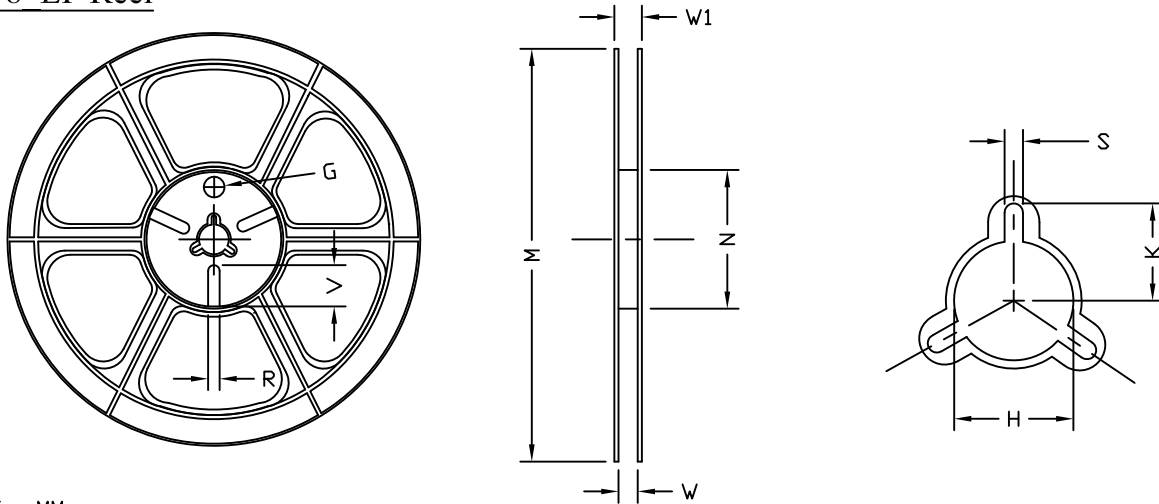
SO8/SO8 EP Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO-8 (12 mm)	6.40 ±0.10	5.20 ±0.10	2.10 ±0.10	1.60 ±0.10	1.50 +0.10	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

SO8/SO8 EP Reel



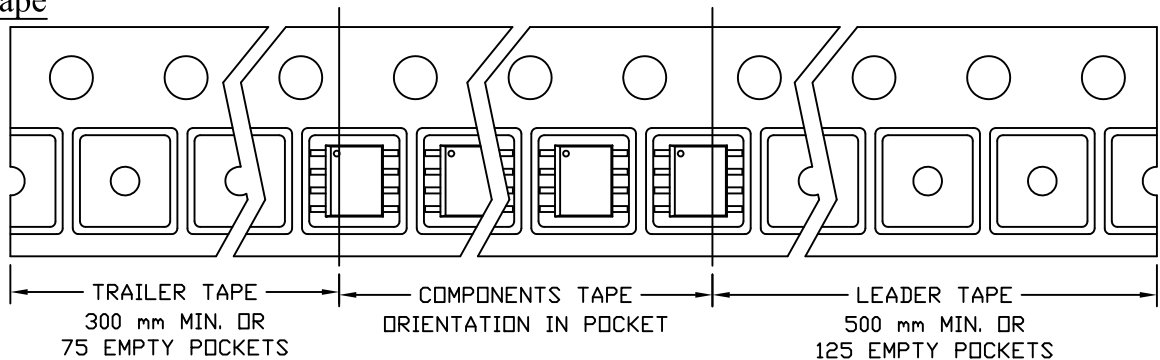
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ø330	ø330.00 ±0.50	ø97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

SO8/SO8 EP Tape

Leader / Trailer
& Orientation

Unit Per Reel:
3000pcs





AOS Semiconductor Product Reliability Report

AO4413, rev E

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com



This AOS product reliability report summarizes the qualification result for AO4413. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4413 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation

I. Product Description:

The AO4413 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- Halogen Free

Detailed information refers to datasheet.

II. Die / Package Information:

	AO4413
Process	Standard sub-micron 30V P-Channel MOSFET
Package Type	SO8
Lead Frame	Cu
Die Attach	Ag epoxy
Bonding	Cu wire
Mold Material	Epoxy resin with silica filler
MSL (moisture sensitive level)	Level 1 based on J-STD-020
Note	* based on information provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4413

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Standard
MSL Precondition	168hr 85°C /85%RH +3 cycle reflow@260°C	-	33 lots	5489pcs	0	JESD22-A113
HTGB	Temp = 150 °c, Vgs=100% of Vgsmax	168hrs 500 hrs 1000 hrs	8 lot 5 lot (Note A*)	1001pcs 77pcs / lot	0	JESD22-A108
HTRB	Temp = 150 °c, Vds=80% of Vdsmax	168hrs 500 hrs 1000 hrs	8 lot 5 lot (Note A*)	1001pcs 77pcs / lot	0	JESD22-A108
HAST	130°C, 85%RH, 33.3 psi, Vgs = 100% of Vgs max	96 hrs	20 lots (Note A*)	1100pcs 55 pcs / lot	0	JESD22-A110
Pressure Pot	121°C, 29.7psi, RH=100%	96 hrs	24lots (Note A*)	1848pcs 77 pcs / lot	0	JESD22-A102
Temperature Cycle	-65°C to 150°C, air to air	250 / 500 cycles	33 lots (Note A*)	2541pcs 77 pcs / lot	0	JESD22-A104

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 3
MTTF = 44613 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4413). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 \times (16 \times 77 \times 500 + 10 \times 77 \times 1000) \times 258] = 3$$

$$\text{MTTF} = 10^9 / \text{FIT} = 3.91 \times 10^8 \text{ hrs} = 44613 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = **Exp**_[Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

K = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K